

L Number	Hits	Search Text	DB	Time stamp
-	2	rupture and oxide and (cmos with "0.13")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/18 08:30
-	37	rupture and (oxide with (thickness or thick)) and (programming or programmable) and tunneling	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/17 15:05
-	925	cmos and (oxide same (tunnel or tunneling)) and write	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/17 15:10
-	0	cmos and (oxide same (tunnel or tunneling)) and (write with swith)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/17 15:11
-	27	rupture and (cmos and (oxide same (tunnel or tunneling)) and write)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/17 15:11
-	2	("4173791").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/18 08:33
-	5	("3744036" "3836992" "4012762" "4051464" "4070687").PN.	USPAT	2003/06/18 08:30
-	0	("antifusesameoxide").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/18 08:33
-	457	antifuse same oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/18 08:34
-	3	memory and (("3744036" "3836992" "4012762" "4051464" "4070687").PN.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/18 09:25
-	249	memory and (antifuse same oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/18 08:35
-	87	(write or writing) and (memory and (antifuse same oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/18 08:41
-	2	("5,480,828").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/18 11:43
-	8	("4543594" "4562639" "4881114" "4943538" "5057451" "5110754" "5635873" "5742555").PN.	USPAT	2003/06/18 09:04
-	8	5742555.URPN.	USPAT	2003/06/18 09:06

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-	28	("3600642" "3883372" "4394674" "4543594" "4689504" "4730129" "5112766" "5252848" "5278787" "5296409" "5306656" "5334880" "5369045" "5371394" "5374843" "5399917" "5414364" "5420450" "5434531" "5465054" "5514608" "5514980" "5536666" "5574303" "5578509" "5583454" "5661048" "5776811").PN.	USPAT	2003/06/18 09:08
-	0	("storageand(writeorwirting)and(readreading)andantifuse") .PN.	USPAT; antifuse	2003/06/18 09:14
-	0	storage and (writeorwirting) and (readreading) and antifuse	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/06/18 09:15
-	311	storage and (write or wirting) and (read or reading) and antifuse	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/06/18 09:15
-	131	oxide and (storage and (write or wirting) and (read or reading) and antifuse)	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/06/18 09:21
-	132	("13" or "0.13" or "13") adj1 CMOS	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/06/18 09:22
-	61	memory and ("13" or "0.13" or "13") adj1 CMOS)	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/06/18 09:25
-	42	5480828.URPN.	USPAT	2003/06/18 09:51
-	0	("antifuseand(readadjlmemoryorrom)andwriteandoxide") .PN.	USPAT; antifuse	2003/06/18 11:44
-	76	antifuse and (read adj1 memory or rom)and write and oxide	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/06/18 14:38
-	38	antifuse same source same drain same (tub or well)	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/06/18 14:39